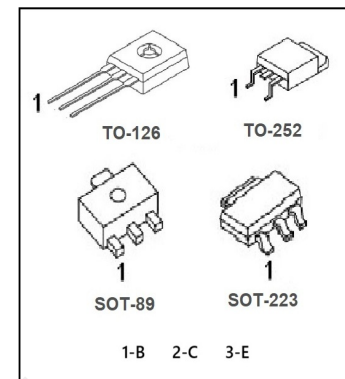
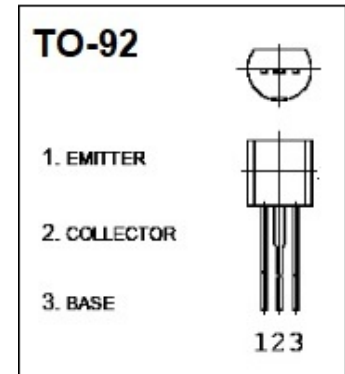


D882

- Complementary to B772
- Package: TO-126/TO-252/SOP-89/SOT-223/TO-92

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating	Unit
Collector-base voltage	BV_{CBO}	40	V
Collector-emitter voltage	BV_{CEO}	30	V
Emitter-base voltage	BV_{EBO}	6	V
Collector current	I_{CM}	3	A
Collector Power Dissipation	P_C	TO-126	1
		TO-252	1.25
		SOP-89	0.5
		SOT-223	1
		TO-92	0.625
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~+150	°C



Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=100\mu A, I_E=0$	40		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=1mA, I_B=0$	30		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=100\mu A, I_C=0$	6		V
collector-base cut-off current	I_{CBO}	$V_{CB}=40V, I_E=0$		1	μA
collector-emitter cut-off current	I_{CEO}	$V_{CE}=30V, I_B=0$		10	μA
emitter-base cut-off current	I_{EBO}	$V_{EB}=6V, I_C=0$		1	μA
DC current gain	H_{FE1}	$V_{CE}=2V, I_C=1A$	60	400	
	H_{FE2}	$V_{CE}=1V, I_C=100mA$	30		
collector-emitter saturation voltage	V_{CESAT}	$I_C=2A, I_B=200mA$		0.5	V
Base-Emitter Saturation Voltage	V_{BESAT}	$I_C=2A, I_B=200mA$		1.2	
Transition frequency	f_T	$V_{CE}=5V, I_C=100mA$	50		MHz

Classification of H_{FE}

Rank	R	Q	P	E
Range	60-120	100-200	160-320	200-400

DDF